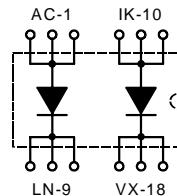


# Fast Recovery Epitaxial Diode (FRED)

## DSEI 2x121

**I<sub>FAVM</sub>** = 2x123 A  
**V<sub>RRM</sub>** = 200 V  
**t<sub>rr</sub>** = 35 ns

V <sub>RSM</sub>	V <sub>RRM</sub>	Type
V	V	
200	200	DSEI 2x 121-02P



Symbol	Conditions	Maximum Ratings (per diode)		
I <sub>FRMS</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	150	A	
I <sub>FAVM</sub> ①	T <sub>C</sub> = 70°C; rectangular; d = 0.5	123	A	
I <sub>FRM</sub>	t <sub>p</sub> < 10 µs; rep. rating; pulse width limited by T <sub>VJM</sub>	600	A	
I <sub>FSM</sub>	T <sub>VJ</sub> = 45°C; t = 10 ms (50 Hz), sine	1200	A	
T <sub>VJ</sub>		-40...+150	°C	
T <sub>VJM</sub>		150	°C	
T <sub>stg</sub>		-40...+150	°C	
P <sub>tot</sub>	T <sub>C</sub> = 25°C	250	W	
V <sub>ISOL</sub>	50/60 Hz, RMS	2500	V~	
	I <sub>ISOL</sub> ≤ 1 mA	3000	V~	
M <sub>d</sub>	Mounting torque (M4)	1.5 - 2.0	Nm	
		14 - 18	lb.in.	
Weight		20	g	

Symbol	Conditions	Characteristic Values (per diode)		
		typ.	max.	
I <sub>R</sub>	T <sub>VJ</sub> = 25°C V <sub>R</sub> = V <sub>RRM</sub>	1	mA	
	T <sub>VJ</sub> = 25°C V <sub>R</sub> = 0.8 • V <sub>RRM</sub>	0.5	mA	
	T <sub>VJ</sub> = 125°C V <sub>R</sub> = 0.8 • V <sub>RRM</sub>	20	mA	
V <sub>F</sub>	I <sub>F</sub> = 120 A; T <sub>VJ</sub> = 150°C	0.89	V	
	T <sub>VJ</sub> = 25°C	1.10	V	
V <sub>T0</sub>	For power-loss calculations only	0.7	V	
r <sub>T</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	2.1	mΩ	
R <sub>thJC</sub>		0.7	K/W	
R <sub>thCK</sub>		0.1	K/W	
t <sub>rr</sub>	I <sub>F</sub> = 1 A; -di/dt = 400 A/µs	35	50	ns
	V <sub>R</sub> = 30 V; T <sub>VJ</sub> = 25°C			
I <sub>RM</sub>	V <sub>R</sub> = 100 V; I <sub>F</sub> = 100 A; -di <sub>F</sub> /dt = 200 A/µs	12	15	A
	L ≤ 0.05 µH; T <sub>VJ</sub> = 100°C			
d <sub>s</sub>	Creeping distance on surface	min. 11.2	mm	
d <sub>A</sub>	Creeping distance in air	min. 11.2	mm	
a	Allowable acceleration	max. 50	m/s <sup>2</sup>	

① I<sub>FAVM</sub> rating includes reverse blocking losses at T<sub>VJM</sub>, V<sub>R</sub> = 0.8 V<sub>RRM</sub>, duty cycle d = 0.5  
Data according to IEC 60747

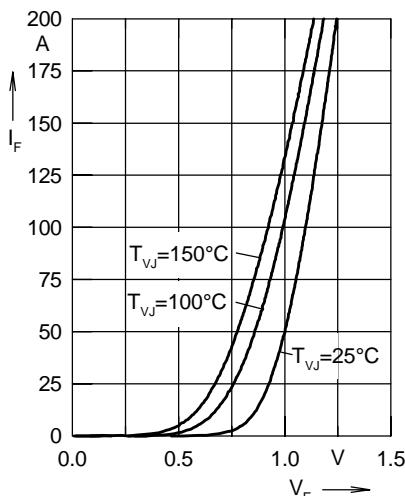
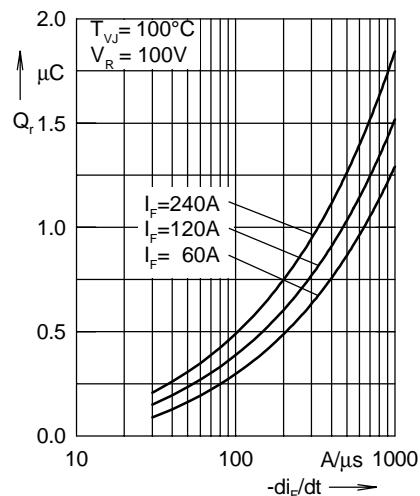
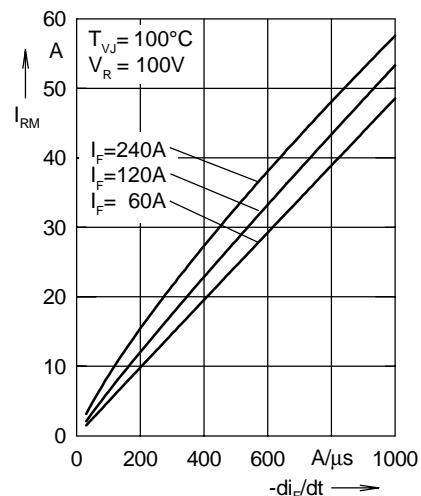
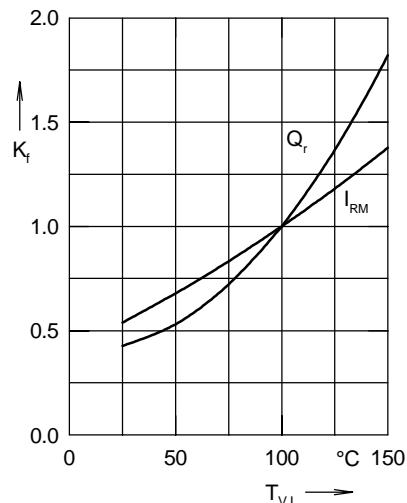
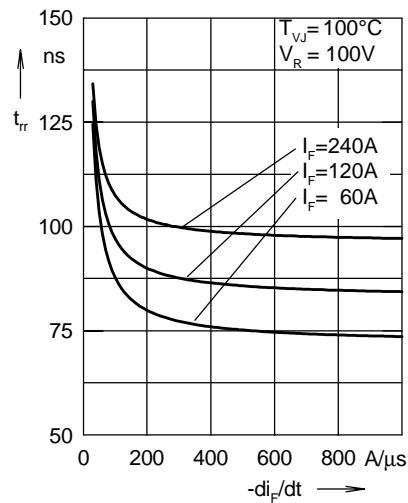
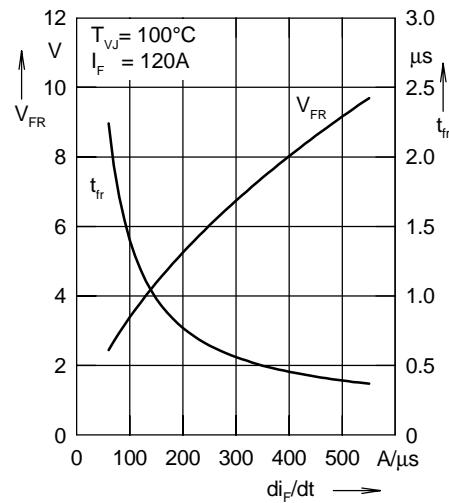
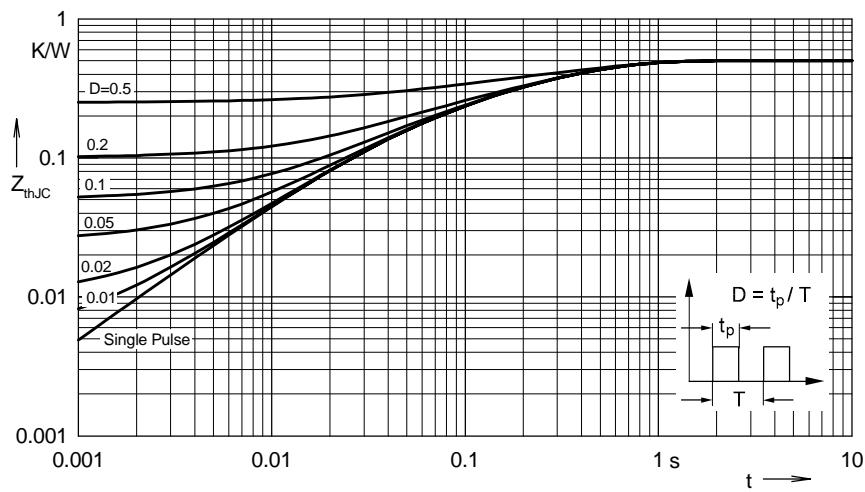
Fig. 1 Forward current  $I_F$  versus  $V_F$ Fig. 2 Typ. reverse recovery charge  $Q_r$  versus  $-di_F/dt$ Fig. 3 Typ. peak reverse current  $I_{RM}$  versus  $-di_F/dt$ Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$ Fig. 5 Typ. recovery time  $t_{rr}$  versus  $-di_F/dt$ Fig. 6 Typ. peak forward voltage  $V_{FR}$  and  $t_{rr}$  versus  $di_F/dt$ 

Fig. 7 Transient thermal impedance junction to case at various duty cycles

Dimensions in mm (1mm = 0.0394")

